



# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

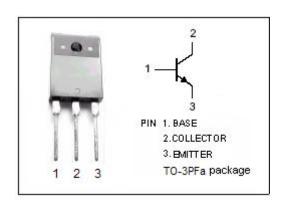
- · Low Collector Saturation Voltage
- High Collector Current
- Good Linearity of h<sub>FE</sub>
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

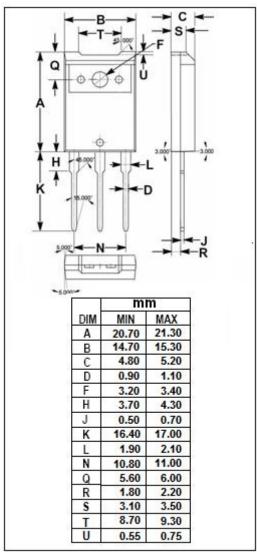
### **APPLICATIONS**

 Designed for switching regulator and high voltage switching applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base voltage	7	V	
Ic	Collector Current-Continuous	20	Α	
lΒ	Base Current-Continuous	6	А	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25℃	125	W	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	3		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	







### isc Silicon NPN Power Transistor

2SC3528

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

10-20 © unios outerwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =20mA ; I <sub>B</sub> =0	400			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 2A			1.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 2A			1.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V ; I <sub>E</sub> = 0			100	μА			
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			100	μА			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2A ; V <sub>CE</sub> = 5V	15						
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A; V <sub>CE</sub> = 5V	10						
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V; f= 1MHz		15		MHz			
Switching times									
t <sub>on</sub>	Turn-On Time				1.0	μ \$			
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 10A; I <sub>B1</sub> = 2.0A, I <sub>B2</sub> = -2.0A; V <sub>CC</sub> = 125V			2.5	μS			
t <sub>f</sub>	Fall Time				1.0	μs			

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